

### MOS FET FK4B01110L

## FK4B01110L Single N-channel MOS FET

For Load switching circuits

#### Features

- Low Drain-source ON resistance:RDS(on) typ. = 57mΩ (VGS = 2.5 V)
- CSP (Chip Size Package)
- RoHS compliant (EU RoHS / MSL:Level 1 compliant)
- Marking Symbol: 1B

#### Packaging

Embossed type (Thermo-compression sealing) : 20 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C				
Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	VDS	12	V	
Gate-Source Voltage	VGS	±8	V	
	ID1 <sup>*1</sup>	2.3		
Drain Current	ID2 <sup>*2</sup>	3.4	А	
	ID3 <sup>*3</sup>	4.1		
	IDp1 <sup>*1*4</sup>	18		
Peak Drain Current	IDp2 <sup>*2*4</sup>	27	А	
	IDp3 <sup>*3*4</sup>	32		
	PD1 <sup>*1</sup>	0.34		
Power Dissipation	PD2 <sup>*2</sup>	0.76	W	
	PD3 <sup>*3</sup>	1.1		
Channel Temperature	Tch	150	С°	
Operating Ambient Temperature	Topr	-40 ~ +85	С°	
Storage Temperature	Tstg	-55 ~ +150	С°	
Nieto Td. ED4 haard (05 America) Adams) Min Ou 00mm <sup>2</sup> Ourseau				





Note \*1 FR4 board (25.4mm×25.4mm×t1.0mm), Min Cu 36mm<sup>2</sup> Copper

\*2 FR4 board (25.4mm×25.4mm×t1.0mm), Full Cu

\*3 Ceramic substrate (70mm×70mm×t1.0mm)

\*4 t = 10  $\mu$ s, Duty Cycle < 1%

## Panasonic

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#### ■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0	12			V
Zero Gate Voltage Drain Current	IDSS	VDS = 12 V, VGS = 0			10	μA
Gate-Source Leakage Current	IGSS	VGS = ±8 V, VDS = 0 V			±10	μA
Gate Threshold Voltage	Vth	ID = 118 μA, VDS =10 V	0.3		1.0	V
Drain-Source ON Resistance	RDS(on)	ID = 1.5 A, VGS = 4.5 V		47	64	mΩ
		ID = 1.0 A, VGS = 2.5 V		57	84	
		ID = 0.5 A, VGS = 1.8 V		70	119	
		ID = 0.25 A, VGS = 1.5 V		91	210	
Input Capacitance <sup>*1</sup>	Ciss	VDS = 10 V		274		
Output Capacitance *1	Coss	VGS = 0		63		pF
Reverse Transfer Capacitance *1	Crss	f = 1MHz		42		
Turn-on delay time *1,*2	td(on)			3.6		
Rise time <sup>*1,*2</sup>	tr	VGS = 0 to 4 5 V		3		ns
Turn-off delay time *1,*2	td(off)	$ID=10\Delta$		34		
Fall time <sup>*1,*2</sup>	tf	10-1.0 A		38		
Total Gate Charge <sup>*1</sup>	Qg	VDD = 6 V		2.55		nC
Gate to Source Charge *1	Qgs	VGS = 4.5 V		0.55		nC
Gate to Drain Miller Charge <sup>*1</sup>	Qgd	ID = 1.0 A		0.55		nC
Body Diode Forward Voltage	VF(D-S)	IF = 0.2A, VGS = 0V		0.6	1.2	V

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

\*1 Guaranteed by design, not subject to production testing

\*2 Measurement circuit for Turn-on delay time / Rise time / Turn-off delay time / Fall time

Electrical State Discharge Characteristics

Standard	Test Type	Symbol	Conditions	Class	Value	Unit
AEC-Q101-001	Human body model	HBM	C = 100 pF, R = 1.5 kΩ	H1B	>500 to $\leq 1k$	V
	Machine model	MM	C = 200 pF, R = 0 $\Omega$	M1B	>50 to ≦ 100	V

Doc No. TT4-EA-14955 Revision. 1



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Note2: Measurement circuit



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IDS - VDS

Dynamic Input/Output Characteristics

Pulse Width tsw (s)

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ALGA004-W-0606-RA01

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Unit: mm

FK4E



Land Pattern (Reference)



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